

**PROBLEM ONE: (60 points)**For Si at 300 K, with  $N_D = 10^{16} \text{ cm}^{-3}$ ,  $N_A \ll N_D$ :NO UNITS FOR  
FINAL ANSWER,  
NO CREDIT THAT PART.

A) (20 points)

Find the equilibrium electron concentration ( $n$ ) in units of  $\text{cm}^{-3}$ .If you say  $n \approx N_D$  10 pointsIf you ~~say~~ say  $n = 10^{16} \text{ cm}^{-3}$  10 pts~~If you say  $n = 10^{16} \text{ cm}^{-3}$  10 pts~~If you don't say  $n \approx N_D$  but still say  
 $n = 10^{16} \text{ cm}^{-3}$ , still get full credit [20 pts.]

B) (20 points)

Find the equilibrium hole concentration ( $p$ ) in units of  $\text{cm}^{-3}$ .

$$p = \frac{n_i^2}{n} \text{ or } \frac{n_i^2}{N_D} \quad 10 \text{ pts.}$$

$$= \frac{[10^{10} \text{ cm}^{-3}]^2}{10^{16} \text{ cm}^{-3}} \quad 5 \text{ pts.}$$

$$= 10^4 \text{ cm}^{-3} \quad 5 \text{ pts.}$$

**PROBLEM ONE: (continued)**

C) (20 points)

Find  $E_C - E_F$  in units of eV. Use whatever method you want.

Sol. #1 5pts  $E_C - E_F = -kT \ln\left[\frac{n}{N_C}\right]$  or equivalent

\* 5pts.  $N_C = 3.2 \times 10^{19} \text{ cm}^{-3}$  or equivalent

(meaning put in #s for  $N_C$  formula correctly)

$E_C - E_F = 0.2 \text{ eV to } 0.21 \text{ eV}$  10pts



~~S.H.H~~

Sol. #2

$$E_F - E_i = kT \ln \left[ \frac{n}{n_i} \right] \quad 5 \text{ pts.}$$

$$E_F - E_i = 0.35 - 0.36 \text{ eV} \quad 5 \text{ pts.}$$

$$E_c - E_i = \frac{E_G}{2} \quad 2 \text{ pts}$$

$$E_c - E_i = \frac{E_G}{2} \pm \frac{3}{4} kT \ln \left[ \frac{m_{pt}}{m_{nt}} \right] \quad 5 \text{ pts}$$

$$E_c - E_i = 0.567 \text{ eV} \pm 1 \text{ meV} \quad 2 \text{ pts}$$

$$E_c - E_i = 0.56 \text{ eV} \pm 1 \text{ meV} \quad 1 \text{ pt}$$

$$E_c - E_F = 0.208 \text{ to } 0.210 \text{ eV}$$
$$= 0.201 \text{ eV to } 0.203 \text{ eV}$$

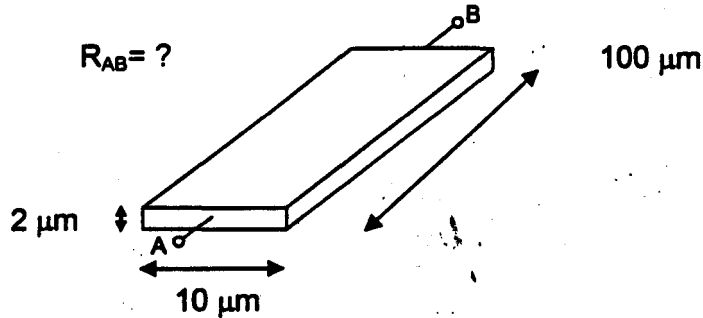
3 pts  
1 pt.

either or  
for credit

either or  
for credit

either or  
for credit

**PROBLEM TWO: (40 points)**



For the silicon sample at  $T = 300 \text{ K}$  shown above, given  $N_D = 10^{16} \text{ cm}^{-3}$ ,  $N_A \ll N_D$ .

A) (20 points)

Find the resistivity  $\rho$  of the Si to within 30% in units of  $\Omega\text{-cm}$ .  
(You may use figure 3.8 from the text.)

Sol #1: graph  $0.4 - 0.6 \Omega\text{-cm}$  20 pts.  
else, 0 pts.

Sol #2: (Back)

B) (20 points)

Calculate the resistance  $R_{AB}$  in units of  $\Omega$ , for the geometry shown above.

If you use both methods, we grade on only method 1.  
(The ~~resistor~~ resistivity method.)

$$R_{AB} = \rho \frac{L}{A} \quad 10 \text{ pts.}$$

$$= 0.5 \Omega\text{-cm} \frac{100 \mu\text{m}}{2 \mu\text{m} \times 10 \mu\text{m}} \quad 5 \text{ pts.} \quad *$$

$$= 25,000 \Omega \quad 5 \text{ pts.}$$

(20,000 - 30,000  $\Omega$  gets 5 pts.)

Sol # 2: Calculate

$$\rho = \frac{1}{nq}$$

5 pts

$$N = 1000 - 1500 \frac{\text{cm}^2}{\text{V-s}}$$

(Fig 3.5) 5 pts.

$$\rho = 0.41 - 0.63 \Omega\text{-cm}$$

6 pts

⊕